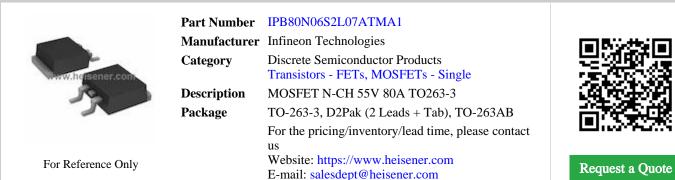


IPB80N06S2L07ATMA1

IPB80N06S2L07ATMA1 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPB80N06S2L07ATMA1 Specifications

Manufacturer Part Number	IPB80N06S2L07ATMA1
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Series	OptiMOS?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	55V
Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Vgs(th) (Max) @ Id	2V @ 150µA
Gate Charge (Qg) (Max) @ Vgs	130nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	3160pF @ 25V
Vgs (Max)	$\pm 20 V$
FET Feature	-
Power Dissipation (Max)	210W (Tc)
Rds On (Max) @ Id, Vgs	6.7 mOhm @ 60A, 10V
Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	PG-TO263-3-2
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
	Report errors?

IPB80N06S2L07ATMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

DISCOVER

IPB80N06S2L07ATMA1 Payment Methods



IPB80N06S2L07ATMA1 Shipping Methods



If you have any question about IPB80N06S2L07ATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com